

FOR USE BY ELECTRICIANS OVERSEAS :

最新トランジスタ規格表 (New Transistor Manual) lists all the transistors registered with the Electronic Industries Association of Japan (EIAJ), arranged in a manner easy to look up. We hope that you will make full use of the data provided in this manual by referring to the Japanese-English translation key given below.

型名	社名	用途	構造	最大定格 (T _b =25°C)					電 気 的 特 性 (T _b =25°C)										外 形	備 考
				V _{ceo} (V)	V _{ceo} (V)	I _c (mA)	P _c (mW)	T _j (°C)	I _{ceo} 最大値 (μA)	直流又はパルスI _{BE}		バイアス		h _{FE}	h _{FE} h _{FE} * (Ω)	h _{FE} h _{FE} * (×10 ⁻⁴)	h _{FE} h _{FE} * (μS)	f _{αB} f _r * (Mc)		
1	2	3	4	5					6		7		8				9	10	11	12

- 1 TYPE NUMBER
- 2 ORIGINAL MANUFACTURER
- 3 USES
- 4 MATERIAL AND STRUCTURE
- 5 MAXIMUM RATINGS
- 6 I_{CBO} MAXIMUM VALUE AND V_{CB} VALUE (CRITERIA FOR MEASURING I_{CBO})
- 7 STANDARD VALUE OF DC/PULSE h_{FE} AND V_{CE}, I_C (CRITERIA FOR MEASURING DC/PULSE h_{FE})
- 8 STANDARD VALUE OF h PARAMETERS AND BIAS V_{CB}, I_E (CRITERIA FOR MEASURING h PARAMETERS)

- * INDICATES VALUE IN GROUNDED-BASE OPERATION, OTHERWISE VALUE IN EMITTER-GROUNDED OPERATION.
 - 9 f_{αB} OF RF CHARACTERISTIC, EXCEPT IN CASE OF * WHICH INDICATES VALUE OF f_r.
 - 10 C_{ob} AND r_{bb'} OF RF CHARACTERISTICS EXCEPT IN CASE OF * IN r_{bb'} COLUMN WHICH INDICATES VALUE OF h_{ie} (real)
 - 11 OUTLINE
 - 12 REMARKS
- :とコンプリ: COMPLEMENTARY TO

型名	社名	用途	構造	最大定格 (T _a = 25°C)					電 氣 的 特 性 (T _a = 25°C)											外 形	備 考		
				V _{CB0} (V)	V _{EB0} (V)	I _C (mA)	P _C (mW)	T _J (°C)	I _{CB0} 最大値		直流又はバラス hFE		バイアス		h _{fe} h _{fb} *	h _{ie} h _{ib} * (Ω)	h _{re} h _{rb} * (×10 ⁻⁴)	h _{oe} h _{ob} * (μU)	f _{ab} f _T * (Mc)			C _{ob} (pF)	r _{bb'} h _{ie(real)} * (Ω)
									μA	V _{CB} (V)	V _{CE} (V)	I _C (mA)	V _{CB} (V)	I _E (mA)									
★ 2SC799	日電	RF. PA	Si. E	80	5	1.5A	10W (T _c = 25°C)	175	1	40	90	10	150	10	-150	250*	15		97B				
★ " 800	"	RF	"	30	4	10	100	150	0.1	25	100	6	2	6	-2	85	1000*	0.5	C _c r _{bb'} = 5 pS	23			
★ " 801	"	RF. PA	Si.TMe	75	5	500	13W (T _c = 25°C)	175	1	50	50	10	150	10	-50	45	100*	32	12*	83			
★ " 802	富士通	PA. SW	Si. EP	60	4	500	1W (T _c = 25°C)	175	5	12	30	4	150	20	-15	180*	5	12*	84B				
★ " 803	"	"	Si. TP	60	4	1.5A	5W (T _c = 25°C)	175	1	12	70	4	400			90*	9	7*	84B				
★ " 804	ソニー	RF. Conv. Mix. Osc	Si. DB	15		20	150	100	0.5	15	50	3	1	6	-4		0.32	40*	24				
★ " 805	"	RF. AF. SW	Si. DB	100	5	200	475	120	1	25	100	5	3	10	-2	160*	3	C _c r _{bb'} = 80 pS	84B				
★ " 806	"	PA	Si.TMe	650	10	10A	125W (T _c = 25°C)	150	5mA	500	30	3	2A	10	-0.5A	50	5*	20	5	102			
★ " 807	"	"	"	650	10	10A	125W (T _c = 25°C)	150	5mA	500	50	3	100	10	-0.5A	50	5*	300	5	102			
★ " 808	"	"	"	300	8	5A	80W (T _c = 25°C)	150	30	50	100	3	2A	10	-500		12*	310	C _c r _{bb'} = 700 pS	102			
" 809	富士通	RF	Si. EP	25	3	20	200	150	0.1	12				6	-2	90	1200*	1.4	40*	50C			
" 810	"	RF. PA	"	40	3	300	500	150	1	35				15	-50	70	750*	3.8	25*	85B			
★ " 811	"	RF	"		4	30	180	175	0.5	15	60	10	2	10	-2		800*	0.9	50	50C			
" 812	"	SW	"	20	4	100	250	150	0.5	10	50	1	10					2.5		49C			
" 813																							
★ " 814	日電	RF. PA	Si. E	30	5	500	400	125	0.2	18	150	5	50	10	-10	140	180*	13	25	44			
★ " 815	"	RF. Osc PA	"	60	5	200	250	125	0.1	45	80	1	50	10	-10	80	200*	5.5	25	138			
★ " 816	三菱	RF	Si. EP	60		1A	1W	200	10	28	100	6	0.1	10	-30		140*	12	C _c r _{bb'} = 60 pS	84B			
★ " 817	"	"	"	30		20	120	150	0.1	12	80	10	1			G _{pe} = 13dB (f = 500MHz, V _{ce} = 6V, I _C = 4mA)				50C			
★ " 818	"	"	Si. TP	160	5	100	800	200			20~180	10	10				100*	4.5	C _c r _{bb'} = 14 pS	84A			
★ " 819	日立	PA	Si. EP	65	4	1A	6W (T _c = 25°C)	175	100	65				28	-100	30	500*	7.5	12	84C			
★ " 820	"	"	"	65	4	1.5A	10W (T _c = 25°C)	175	100	65				28	-100	30	500*	7.5	10	111			
★ " 821	松下	RF. Conv. Mix Osc. PA	"	40	4	300	2.5W (T _c = 25°C)	175	1	20				13.5	-100	70	450*	6.5	15*	84B			
" 822	"	"	"	40	4	500	2.5W (T _c = 25°C)	175	1	20				13.5	-100	70	550*	6.5	15*	84B			
" 823	日電	RF	Si. E	30	3	60	600	150	0.1	10	>30	10	15	10	-15	130	1500*	0.9	C _c r _{bb'} = 3 pS	85B			
" 824	"	"	"	50	3	120	650	150	0.1	10	>20	10	30	10	-50	130	1300*	2.2	C _c r _{bb'} = 4 pS	85B			
" 825	富士通	SW	Si. T	300	6	2A	30W (T _c = 25°C)	175	20	150	75	10	0.5A							99			
" 826	"	RF	Si.TMe	100	6	300	700	175	1	30	100	4	50	30	-10		20*	10	30	84B			
" 827	"	RF. SW	"	100	6	500	700	175	1	30	100	4	50	30	-10		20*	10	30	84B			
" 828	松下	RF. AF	Si. EP	30	5	50	250	125	1	10	65~700	5	2	5	-2	220	3600	0.4	20	220*	2.2	70	138

2SA539 とコンプリ

スタットはインチオン

2SA564 とコンプリ